DISCRETE SEMICONDUCTORS

DATA SHEET

BF510 to 513 N-channel silicon field-effect transistors

Product specification

December 1997



BF510 to 513

DESCRIPTION

Asymmetrical N-channel planar epitaxial junction field-effect transistors in the miniature plastic envelope intended for applications up to the v.h.f. range in hybrid thick and thin-film circuits. Special features are the low feedback capacitance and the low noise figure. These features make the product very suitable for applications such as the r.f. stages in f.m. portables (BF510), car radios (BF511) and mains radios (BF512) or the mixer stage (BF513).

PINNING - SOT23

1 = gate

2 = drain

3 = source

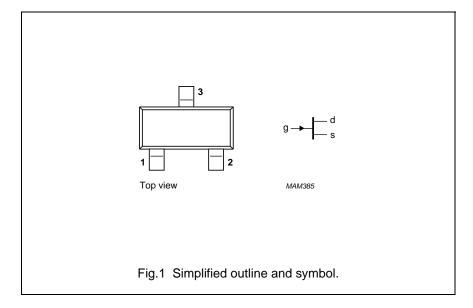
MARKING CODE

BF510 = S6p

BF511 = S7p

BF512 = S8p

BF513 = S9p



QUICK REFERENCE DATA

Drain-source voltage	V _{DS}	max.			20		V
Drain current (DC or average)	I_D	max.	30			mA	
Total power dissipation							
up to $T_{amb} = 40 ^{\circ}C$	P_{tot}	max.	250			mW	
			BF510	511	512	513	
Drain current		>	0.7	2.5	6	10	mA
$V_{DS} = 10 \text{ V}; V_{GS} = 0$	I_{DSS}	<	3.0	7.0	12	18	mA
Transfer admittance (common source)							
$V_{DS} = 10 \text{ V}; V_{GS} = 0; f = 1 \text{ kHz}$	$ y_{fs} $	>	2.5	4	6	7	mS
Feedback capacitance							
$V_{DS} = 10 \text{ V}; V_{GS} = 0$	C_{rs}	typ.	0.3	0.3	_	_	pF
$V_{DS} = 10 \text{ V}; I_{D} = 5 \text{ mA}$	C_{rs}	typ.	_	_	0.3	0.3	pF
Noise figure at optimum source admittance							
$G_S = 1 \text{ mS}$; $-B_S = 3 \text{ mS}$; $f = 100 \text{ MHz}$							
$V_{DS} = 10 \text{ V}; V_{GS} = 0$	F	typ.	1.5	1.5	_	_	dB
$V_{DS} = 10 \text{ V}; I_D = 5 \text{ mA}$	F	typ.	_	_	1.5	1.5	dB

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20	V
Drain-gate voltage (open source)	V_{DGO}	max.	20	V
Drain current (DC or average)	I_D	max.	30	mΑ
Gate current	$\pm I_{G}$	max.	10	mA
Total power dissipation up to T _{amb} = 40 °C (note 1)	P_{tot}	max.	250	mW
Storage temperature range	T_{stg}	-65 to +	150	°C
Junction temperature	T _i	max.	150	°C

THERMAL RESISTANCE

From junction to ambient (note 1)

 $R_{th j-a} = 430 \text{ K/W}$

Note

1. Mounted on a ceramic substrate of 8 mm \times 10 mm \times 0.7 mm.

STATIC CHARACTERISTICS

 $T_{amb} = 25 \, ^{\circ}C$

			BF510	511	512	513	
Gate cut-off current							
$-V_{GS} = 0.2 \text{ V}; V_{DS} = 0$	-I _{GSS}	<	10	10	10	10	nΑ
Gate-drain breakdown voltage							
$I_S = 0$; $-I_D = 10 \mu A$	$-V_{(BR)GDO}$	>	20	20	20	20	V
Drain current $V_{DS} = 10 \text{ V}; V_{GS} = 0$	I _{DSS}	> <	0.7 3.0	2.5 7.0	6 12	_	mA mA
Gate-source cut-off voltage							
$I_D = 10 \mu A; V_{DS} = 10 V$	$-V_{(P)GS}$	typ.	0.8	1.5	2.2	3	V

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DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $V_{DS} = 10 \text{ V}; V_{GS} = 0; T_{amb} = 25 \text{ °C for BF510} \text{ and BF511}$

 V_{DS} = 10 V; I_{D} = 5 mA; T_{amb} = 25 °C for BF512 and BF513

	* DS =	i o v, i _D – v	o iii, i, i amb	- 20 0 10	1 D1 012 a1	IG DI 010	
y-parameters (common source)			BF510	511	512	513	
Input capacitance at f = 1 MHz	C_{is}	<	5	5	5	5	рF
Input conductance at f = 100 MHz	g_{is}	typ.	100	90	60	50	μS
Foodback capacitanes at f = 1 MHz	C_{rs}	typ.	0.4	0.4	0.4	0.4	pF
Feedback capacitance at f = 1 MHz		<	0.5	0.5	0.5	0.5	pF
Transfer admittance at f = 1 kHz	$ y_{fs} $	>	2.5	4.0	4.0	3.5	mS
$V_{GS} = 0$ instead of $I_D = 5$ mA	$ y_{fs} $	>	_	_	6.0	7.0	mS
Transfer admittance at f = 100 MHz	$ y_{fs} $	typ.	3.5	5.5	5.0	5.0	mS
Output capacitance at f = 1 MHz	C_{os}	<	3	3	3	3	pF
Output conductance at f = 1 MHz	g _{os}	<	60	80	100	120	μS
Output conductance at f = 100 MHz	g _{os}	typ.	35	55	70	90	μS
Noise figure at optimum source admittance							
$G_S = 1 \text{ mS}; -B_S = 3 \text{ mS};$							
f = 100 MHz	F	typ.	1.5	1.5	1.5	1.5	dB

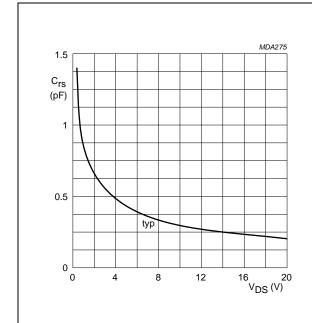
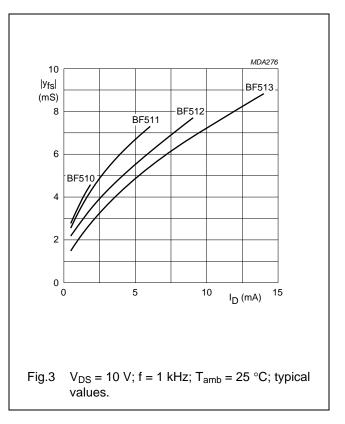
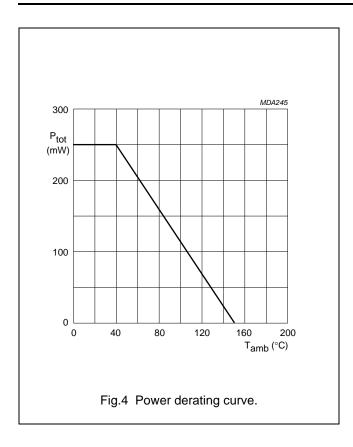


Fig.2 V_{GS} = 0 for BF510 and BF511; I_D = 5 mA for BF512 and BF513; f = 1 MHz; T_{amb} = 25 °C.



BF510 to 513

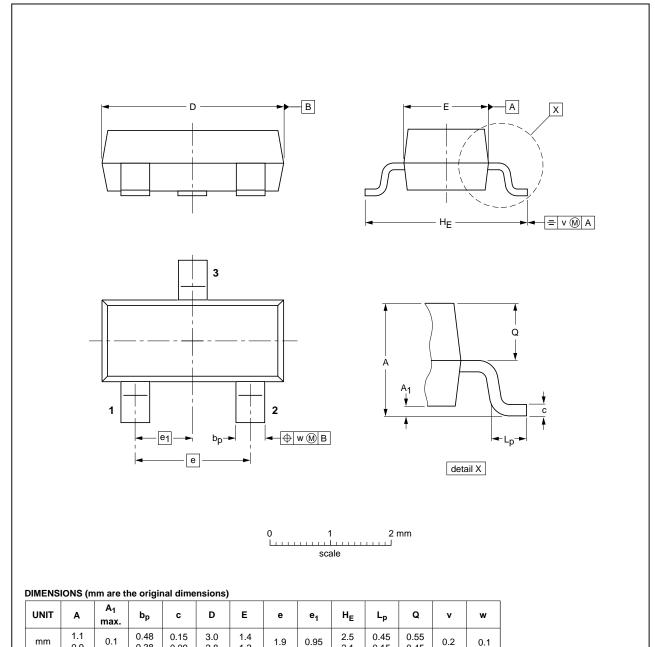


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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE	
SOT23		TO-236AB				-04-11-04 06-03-16	

0.1

0.9

0.38

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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